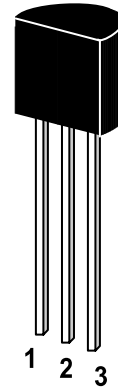


ST 2N6520

PNP Silicon Epitaxial Planar Transistor

for switching and AF amplifier applications.

On special request, these transistors can be manufactured in different pin configurations.

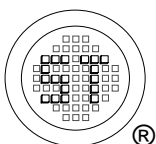


1. Emitter 2. Base 3. Collector

TO-92 Plastic Package
Weight approx. 0.19g

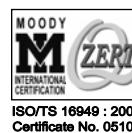
Absolute Maximum Ratings ($T_a = 25^{\circ}\text{C}$)

	Symbol	Value	Unit
Collector Base Voltage	$-V_{\text{CBO}}$	350	V
Collector Emitter Voltage	$-V_{\text{CEO}}$	350	V
Emitter Base Voltage	$-V_{\text{EBO}}$	5	V
Collector Current	$-I_{\text{C}}$	500	mA
Base Current	$-I_{\text{B}}$	250	mA
Power Dissipation	P_{tot}	625	mW
Junction Temperature	T_{j}	150	$^{\circ}\text{C}$
Storage Temperature Range	T_{S}	-55 to +150	$^{\circ}\text{C}$



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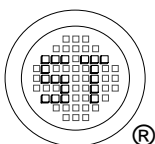


Dated : 07/12/2002

ST 2N6520

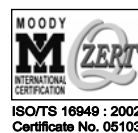
Characteristics at $T_{amb}=25\text{ }^{\circ}\text{C}$

	Symbol	Min.	Typ.	Max.	Unit
DC Current Gain					
at $-V_{CE}=10\text{V}$, $-I_C=1\text{mA}$	h_{FE}	20	-	-	-
at $-V_{CE}=10\text{V}$, $-I_C=10\text{mA}$	h_{FE}	30	-	-	-
at $-V_{CE}=10\text{V}$, $-I_C=30\text{mA}$	h_{FE}	30	-	200	-
at $-V_{CE}=10\text{V}$, $-I_C=50\text{mA}$	h_{FE}	20	-	200	-
at $-V_{CE}=10\text{V}$, $-I_C=100\text{mA}$	h_{FE}	15	-	-	-
Collector Base Breakdown Voltage					
at $-I_C=100\mu\text{A}$	$-BV_{CBO}$	350	-	-	V
Collector Emitter Breakdown Voltage					
at $-I_C=1\text{mA}$	$-BV_{CEO}$	350	-	-	V
Emitter Base Breakdown Voltage					
at $-I_E=10\mu\text{A}$	$-BV_{EBO}$	5	-	-	V
Collector Cutoff Current					
at $-V_{CB}=250\text{V}$	$-I_{CBO}$	-	-	50	nA
Emitter Cutoff Current					
at $-V_{EB}=4\text{V}$	$-I_{EBO}$	-	-	50	nA
Collector Base Capacitance					
at $-V_{CB}=20\text{V}$, $f=1\text{MHz}$	C_{cb}	-	-	6	pF
Emitter Base Capacitance					
at $-V_{EB}=0.5\text{V}$, $f=1\text{MHz}$	C_{eb}	-	-	100	pF
Base Emitter Saturation Voltage					
at $-I_C=10\text{mA}$, $-I_B=1\text{mA}$	$-V_{BE(sat)}$	-	-	0.75	V
at $-I_C=20\text{mA}$, $-I_B=2\text{mA}$	$-V_{BE(sat)}$	-	-	0.85	V
at $-I_C=30\text{mA}$, $-I_B=3\text{mA}$	$-V_{BE(sat)}$	-	-	0.9	V
Collector Emitter Saturation Voltage					
at $-I_C=10\text{mA}$, $-I_B=1\text{mA}$	$-V_{CE(sat)}$	-	-	0.3	V
at $-I_C=20\text{mA}$, $-I_B=2\text{mA}$	$-V_{CE(sat)}$	-	-	0.35	V
at $-I_C=30\text{mA}$, $-I_B=3\text{mA}$	$-V_{CE(sat)}$	-	-	0.5	V
at $-I_C=50\text{mA}$, $-I_B=5\text{mA}$	$-V_{CE(sat)}$	-	-	1	V
Base Emitter On Voltage					
at $-V_{CE}=10\text{V}$, $-I_C=100\text{mA}$	$-V_{BE(on)}$	-	-	2	V
Current Gain Bandwidth Product					
at $-V_{CE}=20\text{V}$, $-I_C=10\text{mA}$, $f=20\text{MHz}$	f_T	40	-	200	MHz
Turn On Time					
at $-V_{BE(off)}=2\text{V}$, $-V_{CC}=100\text{V}$ $-I_C=50\text{mA}$, $-I_{B1}=10\text{mA}$	t_{on}	-	-	200	ns
Turn Off Time					
at $-V_{CC}=100\text{V}$, $-I_C=50\text{mA}$, $-I_{B1}=-I_{B2}=10\text{mA}$	t_{off}	-	-	3.5	ns



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ISO/TS 16949 : 2002
Certificate No. 05103



ISO 14001:2004
Certificate No. 7116



ISO 9001:2000
Certificate No. 0506098

Dated : 07/12/2002